

SGL100T65SFD / SGL100T60SFD

650V / 600V 100A FieldStop Trench

IGBT

Features

- FieldStop Trench Technology, Positive temperature coefficient
- $V_{CE(sat)}=1.53V@I_C=100A$
- $t_r=60ns(typ.)$
- High Speed Switching & Low Power Loss
- High Input Impedance

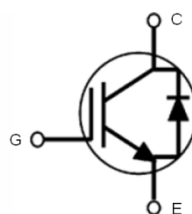
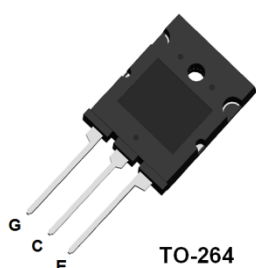
Applications

- UPS, Inverter

Description

The device is designed by advanced FieldStop Trench technology process. This IGBT offer low $V_{CE(sat)}$, high speed switching performance and excellent quality for application such as UPS, inverter and other switching applications.

Package Type & Internal Circuit



Absolute Maximum Ratings

Symbol	Parameter		Ratings	Unit
V _{CES}	Collector to Emitter Voltage		600	V
V _{GES}	Gate to Emitter Voltage		± 20	V
I _C	Collector Current	T _C =25℃	100	A
		T _C =100℃	50	A
I _{CM}	Pulsed Collector Current		180	A
I _F	Diode Continuous Forward Current	T _C =100℃	25	A
I _{FM}	Diode Maximum Forward Current		250	A
P _D	Maximum Power Dissipation	T _C =25℃	310	W
		T _C =100℃	100	W
T _J	Operating Junction Temperature Range		-55~+150	℃
T _{STG}	Storage Temperature Range		-55~+150	℃

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
$R_{th(J-C)}(IGBT)$	Thermal Resistance, Junction to case for IGBT	0.36	$^{\circ}C/W$
$R_{th(J-C)}(Diode)$	Thermal Resistance, Junction to case for Diode	0.8	$^{\circ}C/W$
$R_{th(J-A)}$	Thermal Resistance, Junction to Ambient	26	$^{\circ}C/W$

**Electrical Characteristics of IGBT** @ $T_C=25\text{ }^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{CES}	Collector to Emitter Breakdown Voltage	$V_{GE}=0V, I_C=250\mu A$	600	-	-	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=100A, V_{GE}=15V$	-	1.53	2	V
		$I_C=100A, V_{GE}=15V, T_C=150^{\circ}\text{C}$	-	1.77	-	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{CE}=V_{GE}, I_C=250\mu A$	4.5	5.6	6.5	V
I_{CES}	Zero Gate Voltage Collector Current	$V_{CE}=V_{CES}, V_{GE}=0V$	-	-	100	μA
I_{GES}	Gate to Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0V$	-	-	± 250	nA

Electrical Characteristics of Diode @ $T_C=25\text{ }^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=25A$	-	1.75	3.9	V
		$I_F=25A, T_C=150^{\circ}\text{C}$	-	2.5	-	V
t_{rr}	Diode Reverse Recovery Time	$I_F=25A, di/dt=-200A/\mu s$	-	120	-	ns
I_{rr}	Diode Peak Reverse Recovery Current		-	9.7	-	A
Q_{rr}	Diode Reverse Recovery Charge		-	560	-	nC

Switching Characteristics @ $T_C=25\text{ }^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$I_C=100A, V_{CC}=300V, V_{GE}=15V, R_G=10\Omega$ Inductive Load, $T_C=25^{\circ}\text{C}$	-	76	-	ns
t_r	Rising Time		-	174	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	284	-	ns
t_f	Falling Time		-	58	-	ns
E_{on}	Turn-on Switching Loss		-	2.59	-	mJ
E_{off}	Turn-off Switching Loss		-	3.04	-	mJ
E_{ts}	Total Switching Loss	$I_C=100A, V_{CC}=300V, V_{GE}=15V, R_G=10\Omega$ Inductive Load, $T_C=150^{\circ}\text{C}$	-	5.63	-	mJ
$t_{d(on)}$	Turn-on Delay Time		-	77	-	ns
t_r	Rising Time		-	202	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	296	-	ns
t_f	Falling Time		-	279	-	ns
E_{on}	Turn-on Switching Loss		-	2.8	-	mJ
E_{off}	Turn-off Switching Loss	$V_{GE}=0V, V_{CE}=30V, f=1.0MHz$	-	4.32	-	mJ
E_{ts}	Total Switching Loss		-	7.12	-	mJ
C_{ies}	Input Capacitance		-	5800	-	pF
C_{res}	Reverse Transfer Capacitance	$I_C=100A, V_{CC}=300V, V_{GE}=15V$	-	280	-	pF
C_{oes}	Output Capacitance		-	700	-	pF
Q_g	Total Gate Charge		-	350	-	nC
Q_{ge}	Gate to Emitter Charge	$V_{CC}=300V, V_{GE}=15V$	-	65	-	nC
Q_{gc}	Gate to Collector Charge		-	110	-	nC
t_{sc}	Short Circuit Withstand Time	$V_{CC}=300V, V_{GE}=15V$	10	-	-	μs

Typical Performance Characteristics

Fig. 1. Typical Output Characteristics

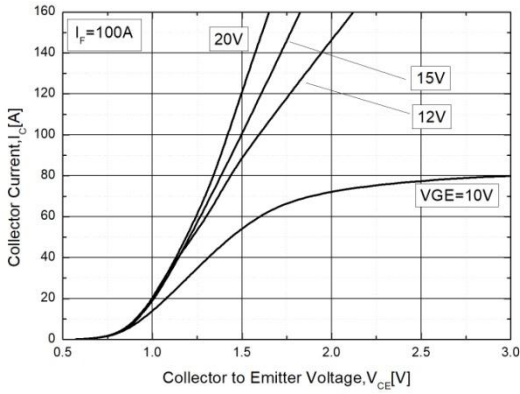


Fig. 2. Typical Saturation Voltage Characteristics

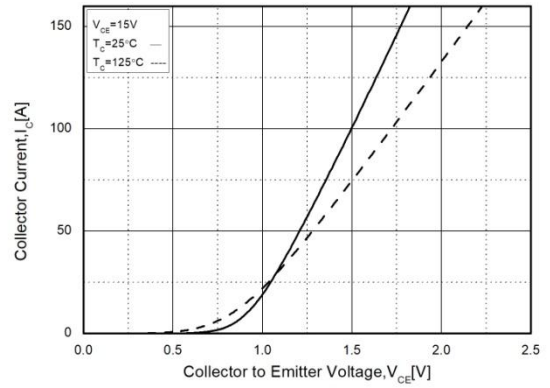


Fig. 3. Typical Saturation Voltage vs. T_C

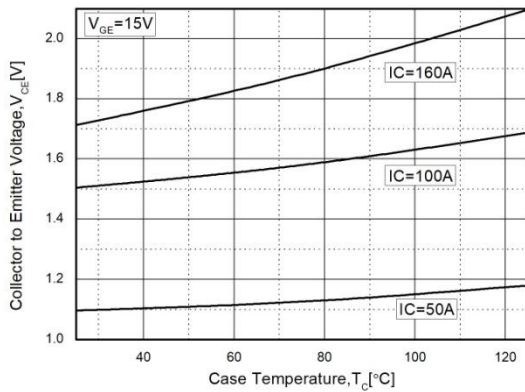


Fig. 4. Diode Forward Characteristics

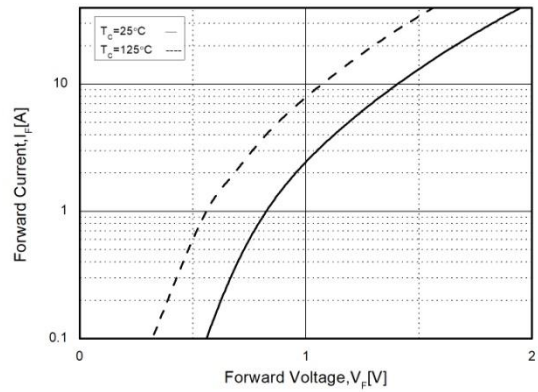


Fig. 5. Typical Capacitance Characteristics

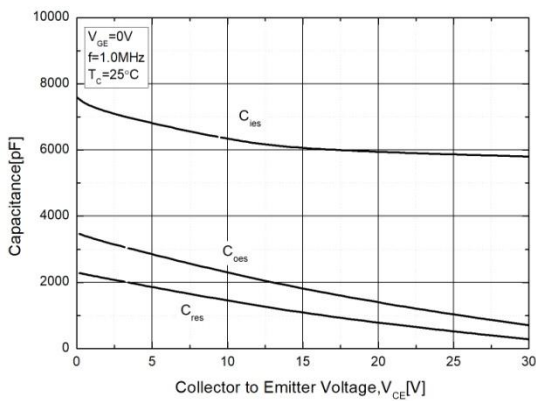
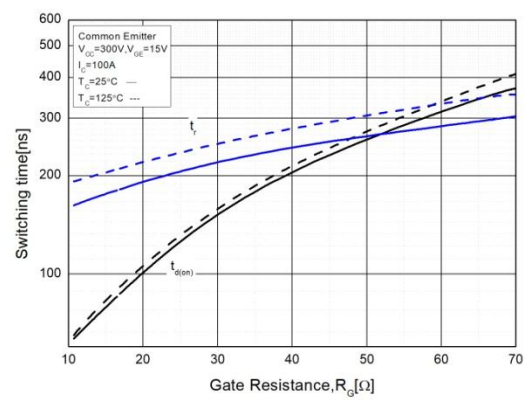


Fig. 6. Turn-on Characteristics vs. R_G



Typical Performance Characteristics

Fig. 7. Turn-off Characteristics vs. R_G

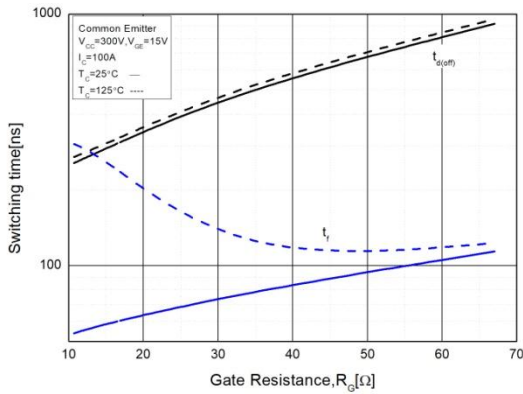


Fig. 8. Switching Loss vs. R_G

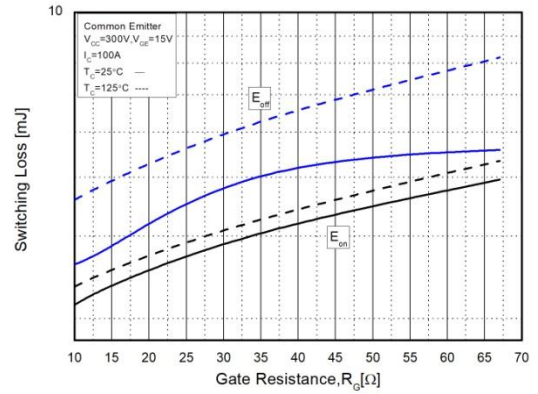


Fig. 9. Turn-on Characteristics vs. I_C

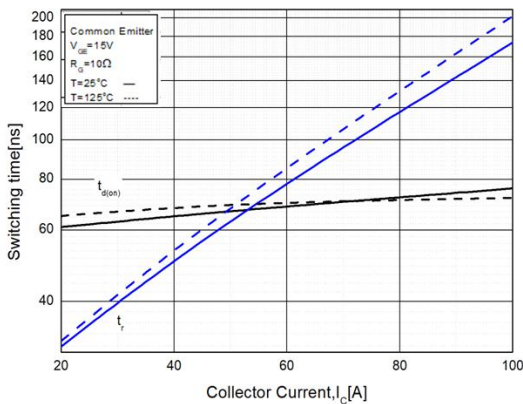


Fig. 10. Turn-off Characteristics vs. I_C

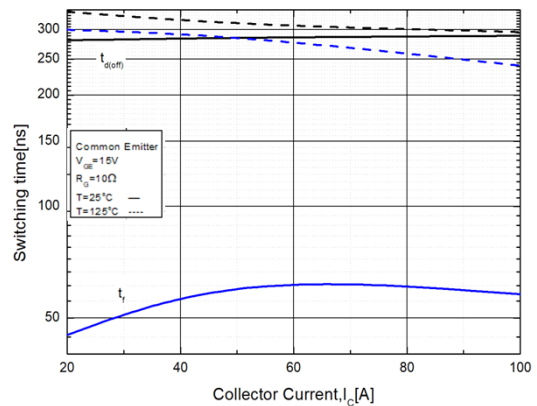
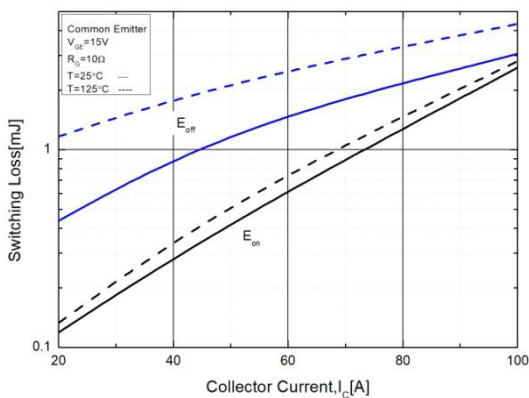


Fig. 11. Switching Loss vs. I_C



Package Dimensions

TO-264

(Dimensions in Millimeters)

